

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-0043

2. Structure :

- 2-1. Planar type : PIN diode.
- 2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy .

3. Size :

- 3-1. Chip size : 43 mils × 43 mils (1.095 mm × 1.095 mm).
- 3-2. Chip thickness : 12 ± 1.5mils (0.305 ± 0.038mm).
- 3-3. Active area : 35.24 mils × 35.24 mils (0.895 mm × 0.895 mm).
- 3-4. Bonding pad (Anode) : 6.30 mils (0.160 mm) diameter.
- 3-5. Pattern drawing : Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			10	nA
*Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	60			V
Open circuit voltage	V_{oc}	$T=2856K$ $E_e=5mW/cm^2$		350		mV
Short circuit Current	I_{sc}	$T=2856K$ $E_e=5mW/cm^2$		8		μA
Reverse light current	I_L	$V_R=5V$ $T=2856K$ $E_e=5mW/cm^2$		8		μA
Total Capacitance	C_t	$V_R=5V$ $E_e=0mW/cm^2$ $f=1MHz$		2.5		pF

*Based on 100% probing

